



**ES2AB-ES2JB**

**Feature**

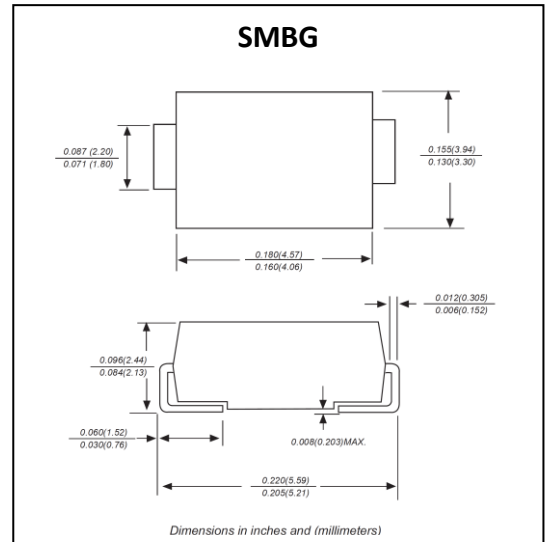
- $I_o$  2A
- $V_{RRM}$  50V-600V
- Glass passivated chip
- High surge current capability

**Application**

- Rectifier

**Marking**

- ES2X X: From A to J



**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	ES2								Unit	
		I	A	B	C	D	E	G	H		J
Repetitive Peak Reverse Voltage	$V_{RRM}$		50	100	150	200	300	400	500	600	V
Maximum RMS Voltage	$V_{RMS}$		35	70	105	140	210	280	350	420	V
Average Forward Current 60HZ Half-sine wave, Resistance load, $T_L=110^\circ\text{C}$	$I_{F(AV)}$		2								A
Non-repetitive Peak Forward Surge Current 60Hz Half-sine wave ,1 cycle , $T_a =25^\circ\text{C}$	$I_{FSM}$		50								A
Junction Temperature	$T_J$		-55 ~ +150								$^\circ\text{C}$
Storage Temperature	$T_{STG}$		-55 ~ +150								$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	ES2								Unit		
			A	B	C	D	E	G	H	J			
Peak Forward Voltage	$V_F$	$I_F = 2A$	0.95				1.25	1.70			V		
Maximum reverse recovery time	$t_{rr}$	$I_F=0.5A, I_R=1.0A, I_{rr}=0.25A$	35								ns		
Peak Reverse Current	$I_{RRM1}$	$V_{RM}=V_R$	$T_a=25^\circ\text{C}$		5								$\mu\text{A}$
	$I_{RRM2}$	$R_M$	$T_a=100^\circ\text{C}$		100								$\mu\text{A}$
Thermal Resistance(Typical)	$R_{\theta J-A}$	Between junction and ambient	75								$^\circ\text{C/W}$		
	$R_{\theta J-L}$	Between junction and terminal	20								$^\circ\text{C/W}$		

**Typical Characteristics**

FIG.1: FORWARD CURRENT DERATING CURVE

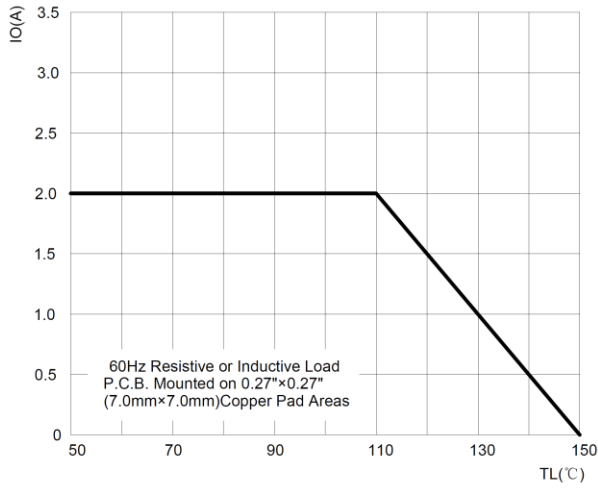


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

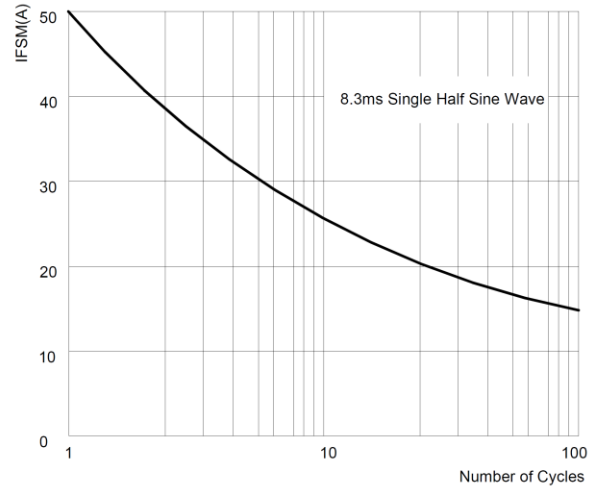


FIG.3: TYPICAL FORWARD CHARACTERISTICS

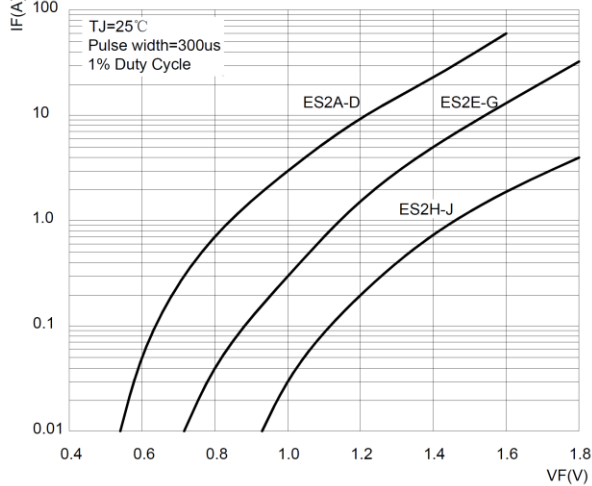


FIG.4: TYPICAL REVERSE CHARACTERISTICS

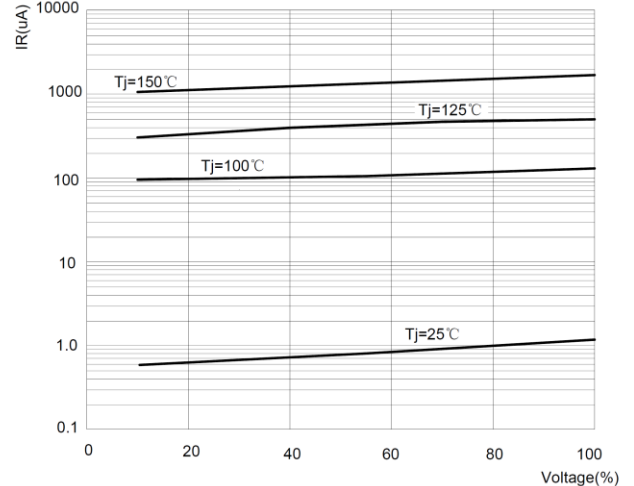
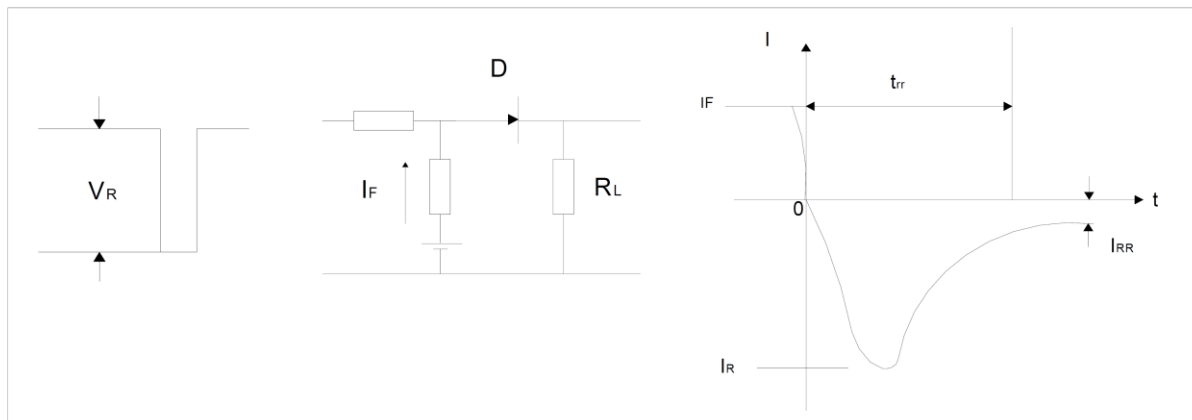


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)